

## N-CHANNEL SILICON POWER MOSFET

## FAP-IIIB SERIES

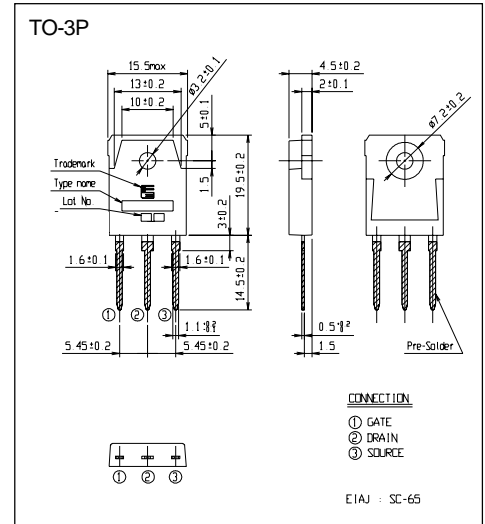
### ■ Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- High voltage
- Avalanche-proof

### ■ Applications

- Switching regulators
- DC-DC converters
- General purpose power amplifier

### ■ Outline Drawings



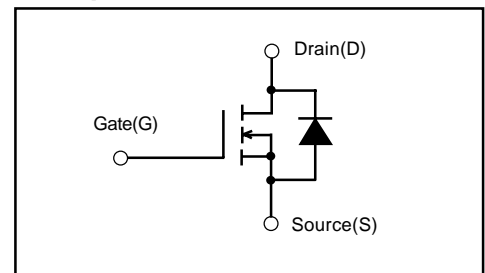
### ■ Maximum ratings and characteristics

#### ● Absolute maximum ratings (Tc=25°C unless otherwise specified)

Item	Symbol	Rating	Unit	Remarks
Drain-source voltage	V <sub>DS</sub>	60	V	
Continuous drain current	I <sub>D</sub>	±100	A	
Pulsed drain current	I <sub>D</sub> [puls]	±400	A	
Gate-source peak voltage	V <sub>GS</sub>	±20	V	
Maximum avalanche energy	E <sub>AV</sub>	1268.3	mJ	*1
Maximum power dissipation	P <sub>D</sub>	150	W	
Operating and storage temperature range	T <sub>ch</sub>	+150	°C	
	T <sub>stg</sub>	-55 to +150	°C	

\*1 L=0.169mH, V<sub>CC</sub>=24V

### ■ Equivalent circuit schematic



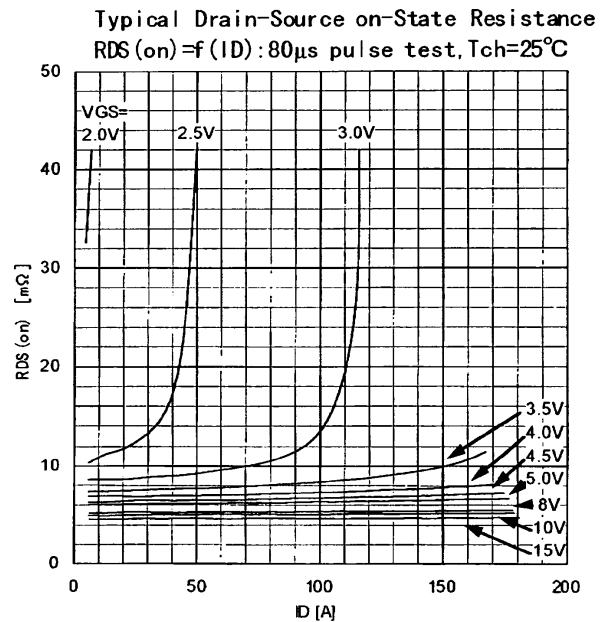
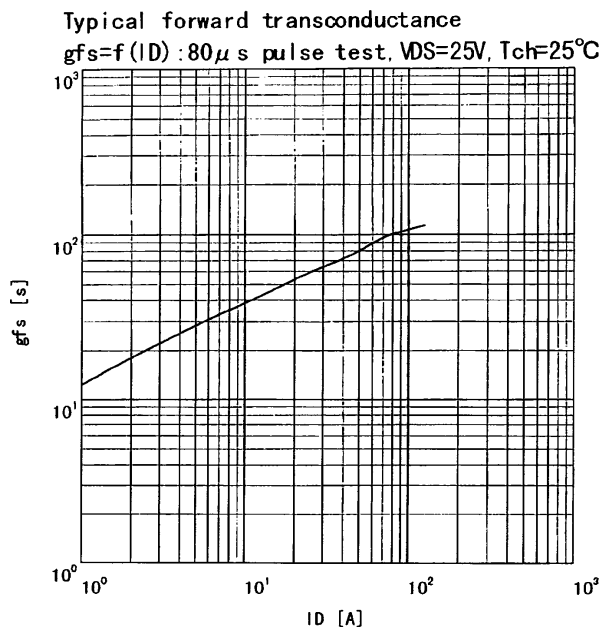
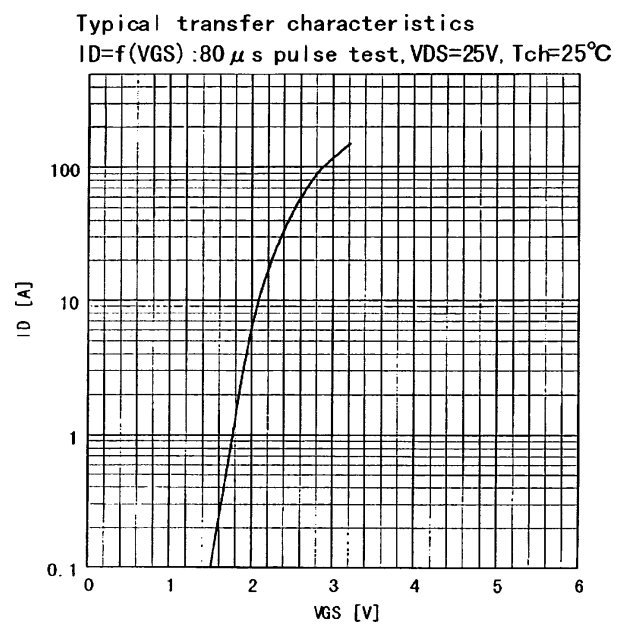
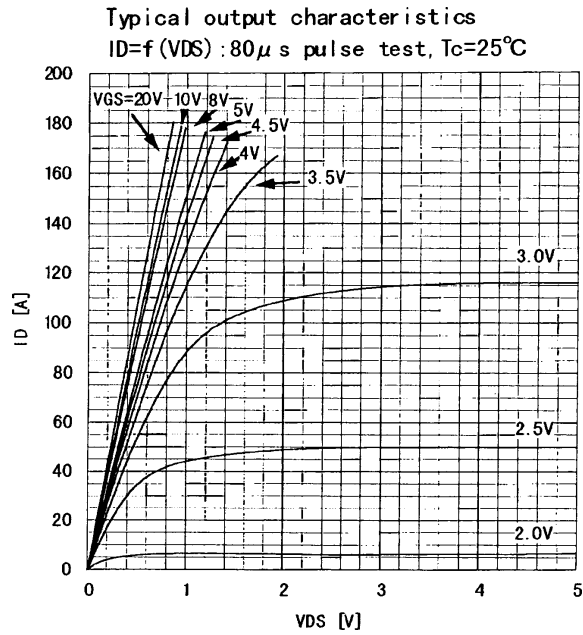
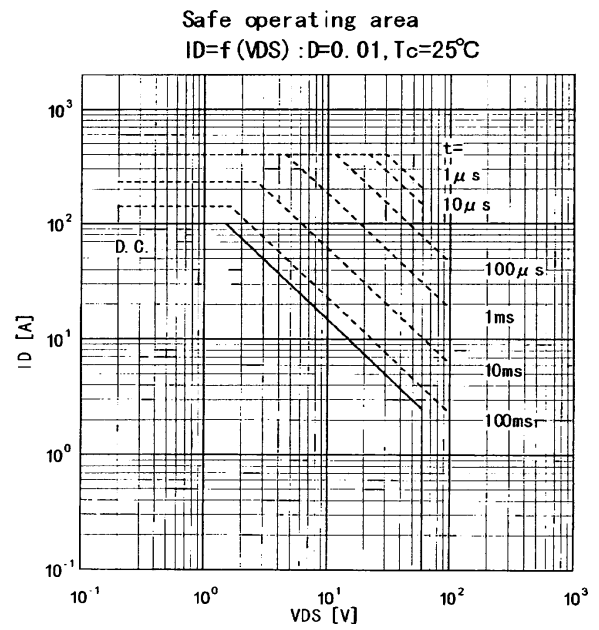
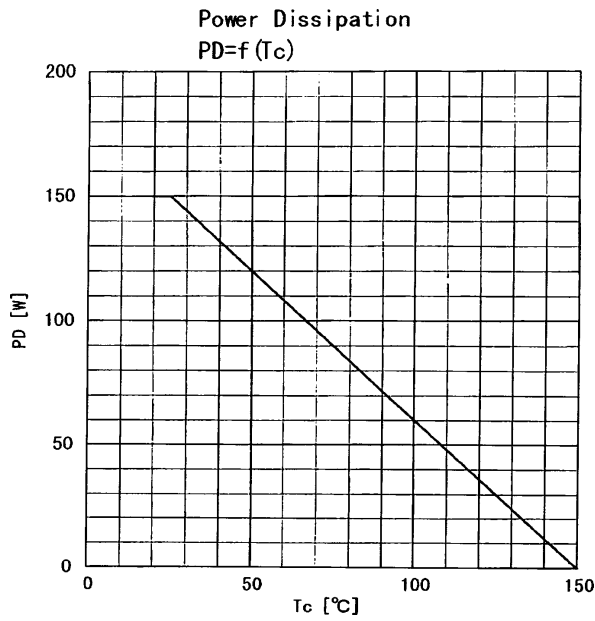
#### ● Electrical characteristics (Tc =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA V <sub>GS</sub> =0V	60			V	
Gate threshold voltage	V <sub>GS(th)</sub>	I <sub>D</sub> =1mA V <sub>DS</sub> =V <sub>GS</sub>	1.0	1.5	2.0	V	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =60V V <sub>GS</sub> =0V	T <sub>ch</sub> =25°C		10	500	μA
			T <sub>ch</sub> =125°C		0.2	1.0	mA
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V V <sub>DS</sub> =0V		10	100	nA	
Drain-source on-state resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =50A V <sub>GS</sub> =10V	V <sub>GS</sub> =4V		7.0	11.0	mΩ
			V <sub>GS</sub> =10V		5.0	6.5	mΩ
Forward transconductance	g <sub>fs</sub>	I <sub>D</sub> =50A V <sub>DS</sub> =25V	40	80		S	
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V		6700	10050	pF	
Output capacitance	C <sub>oss</sub>	V <sub>GS</sub> =0V		2100	3150		
Reverse transfer capacitance	C <sub>rss</sub>	f=1MHz		570	860		
Turn-on time	t <sub>d(on)</sub>	V <sub>CC</sub> =30V R <sub>G</sub> =10 Ω		20	30	ns	
	t <sub>r</sub>		I <sub>D</sub> =100A		160		300
Turn-off time	t <sub>d(off)</sub>	V <sub>GS</sub> =10V		410	620		
	t <sub>f</sub>			330	500		
Avalanche capability	I <sub>AV</sub>	L=100μH T <sub>ch</sub> =25°C	100			A	
Diode forward on-voltage	V <sub>SD</sub>	I <sub>F</sub> =100A V <sub>GS</sub> =0V T <sub>ch</sub> =25°C		1.0	1.5	V	
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> =50A		85		ns	
Reverse recovery charge	Q <sub>rr</sub>	-di/dt=100A/μs T <sub>ch</sub> =25°C		0.21		μC	

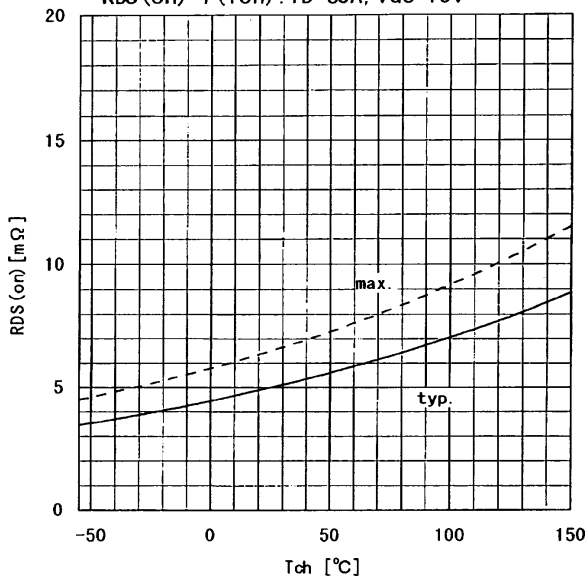
#### ● Thermal characteristics

Item	Symbol	Min.	Typ.	Max.	Units
Thermal resistance	R <sub>th(ch-c)</sub>			0.83	°C/W
	R <sub>th(ch-a)</sub>			35.0	°C/W

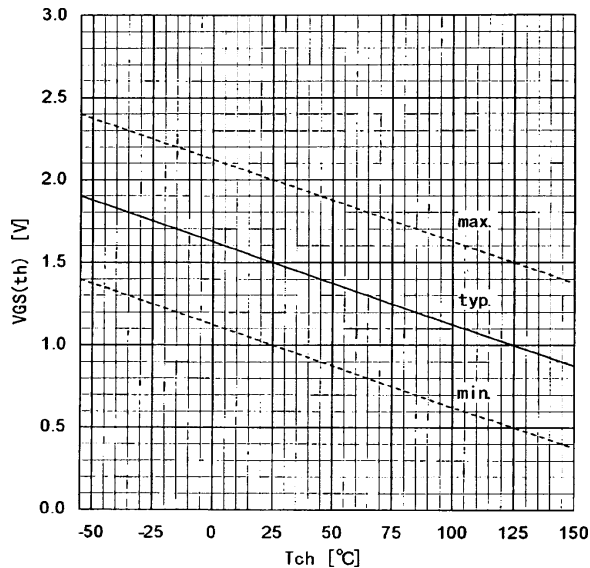
Characteristics



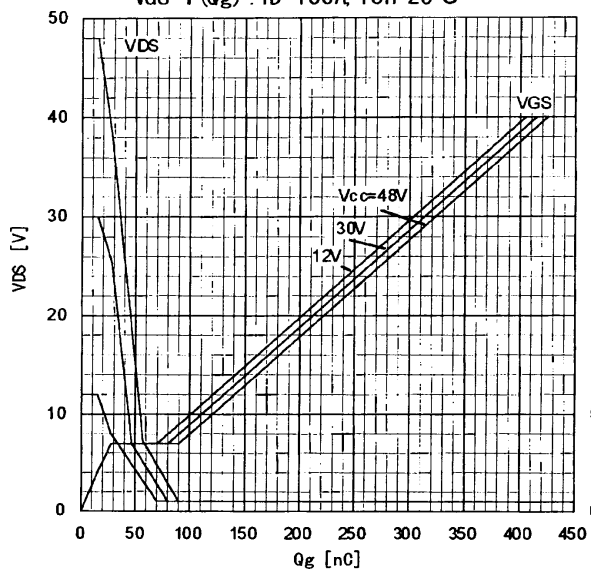
Drain-source on-state resistance  
 $R_{DS(on)} = f(T_{ch}) : I_D = 50A, V_{GS} = 10V$



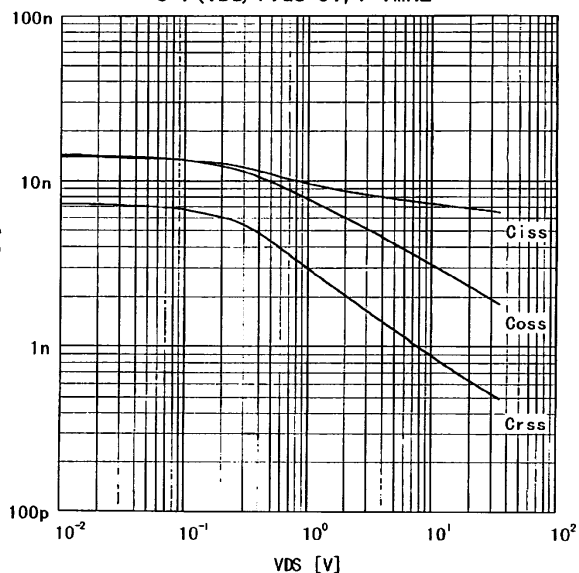
Gate Threshold Voltage vs. Tch  
 $V_{GS(th)} = f(T_{ch}) : V_{DS} = V_{GS}, I_D = 1mA$



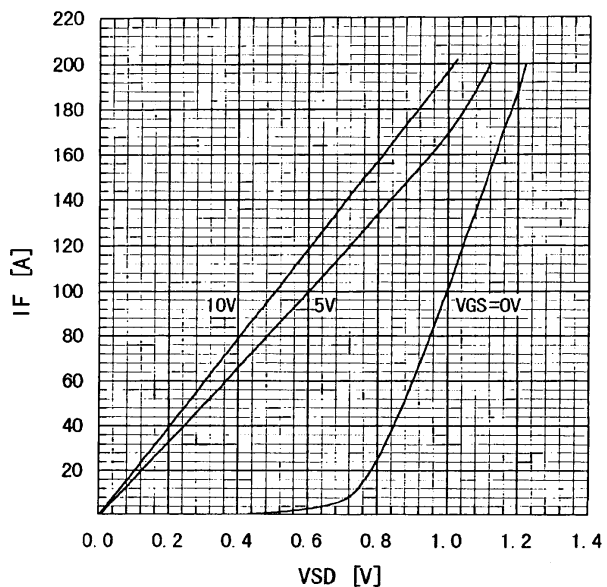
Typical Gate Charge Characteristics  
 $V_{GS} = f(Q_g) : I_D = 100A, T_{ch} = 25°C$



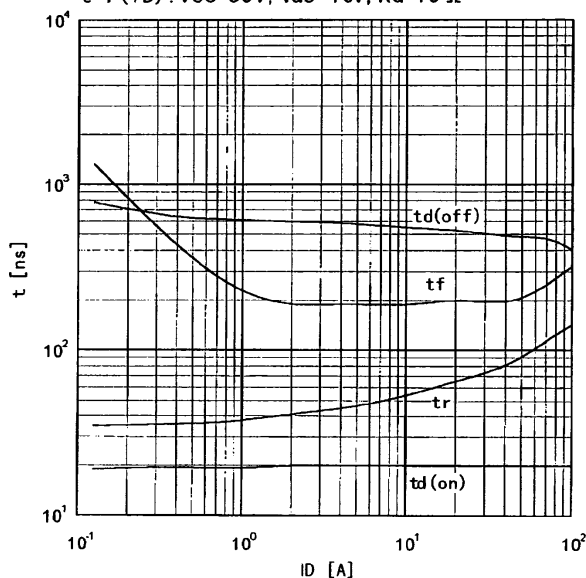
Typical capacitances  
 $C = f(V_{DS}) : V_{GS} = 0V, f = 1MHz$



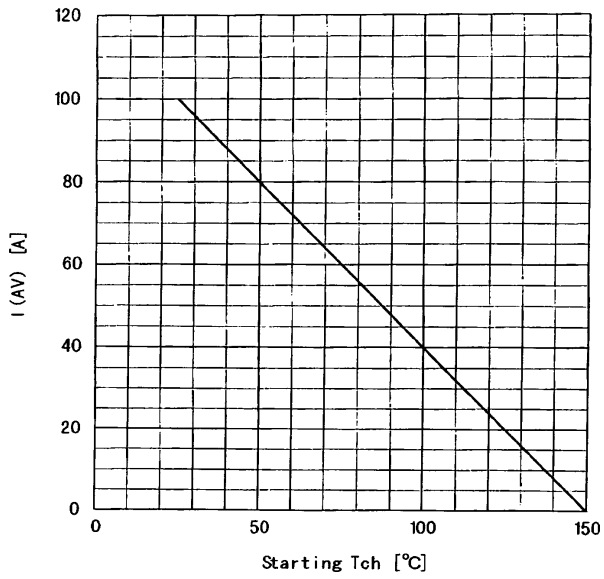
Typical Forward Characteristics of Reverse Diode  
 $I_F = f(V_{SD}) : 80\mu s \text{ pulse test}, T_{ch} = 25°C$



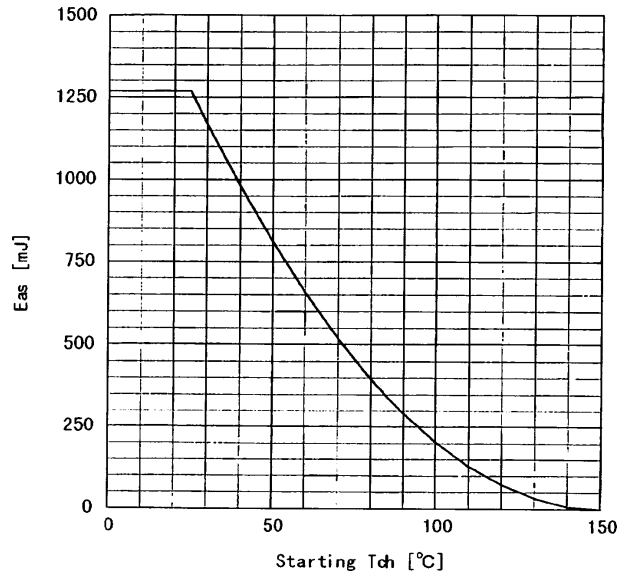
Typical Switching Characteristics vs. ID  
 $t = f(I_D) : V_{CC} = 30V, V_{GS} = 10V, R_G = 10\Omega$



Maximum Avalanche Current vs. starting Tch  
 $I_{AV} = f(\text{starting Tch})$



Maximum Avalanche energy vs. starting Tch  
 $E_{as} = f(\text{starting Tch}) : V_{cc} = 24V, I_{AV} \leq 100A$



Transient thermal impedance  
 $Z_{thch} = f(t)$  parameter:  $D = t/T$

